

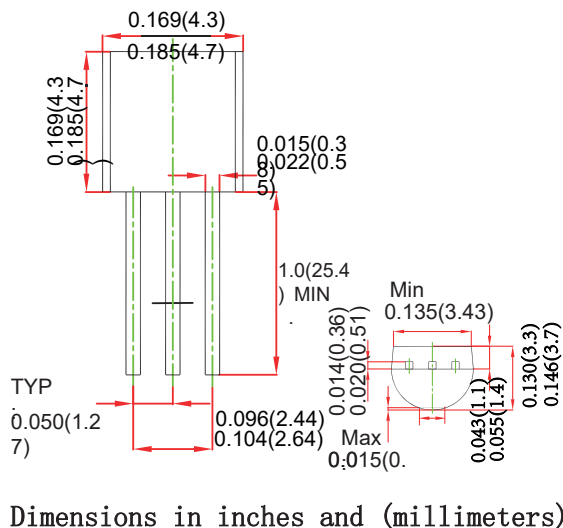
TO-92 Plastic-Encapsulate Transistors

FEATURES

- Low Collector-Emitter Saturation Voltage
- High voltage
- PNP Transistors

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



Dimensions in inches and (millimeters)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-0.15	A
P_D	Collector Power Dissipation	0.4	W
T_J	Junction Temperature	150	°C
T_{Stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}$, $I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}$, $I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_C=-100\mu\text{A}$, $I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50\text{V}$, $I_E=0$			-100	nA
Collector cut-off current	I_{CEO}	$V_{CE}=-50\text{V}$, $I_B=0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}$, $I_C=0$			-100	nA
DC current gain	$H_{FE(1)}$	$V_{CE}=-6\text{V}$, $I_C=-2\text{mA}$	70		400	
	$H_{FE(2)}$	$V_{CE}=-6\text{V}$, $I_C=-150\text{mA}$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}$, $I_B=-10\text{mA}$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-100\text{mA}$, $I_B=-10\text{mA}$			-1.1	V
Gain Bandwidth Product	f_T	$V_{CE}=-10\text{V}$, $I_C=-1\text{mA}$, $f=30\text{MHz}$	80			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}$, $I_E=0$, $f=1\text{MHz}$			7	pF
Noise figure	NF	$V_{CE}=-6\text{V}$, $I_C=-0.1\text{mA}$, $f=1\text{KHz}$ $R_G=10\text{K}\Omega$			6	dB

CLASSIFICATION OF $H_{FE(1)}$

RANK	O	Y	GR
RANGE	70-140	120-240	200-400

RATINGS AND CHARACTERISTIC CURVES

